L Number	Hits	Search Text	DB	Time stamp
-	659	(216/2).CCLS.	USPAT; US-PGPUB	2003/05/01 09:46
-	141	((216/2).CCLS.) and (void or release or cavity) and silicon adj dioxide	USPAT; US-PGPUB	2003/05/27 13:27
-	70	((216/2).CCLS.) and (void or release or cavity) and MEMS	USPAT; US-PGPUB	2003/05/01 10:02
-	264	((216/2).CCLS.) and silicon adj dioxide	USPAT; US-PGPUB	2003/04/29 09:27
-	517	mems and sacrificial and (cavity or void)	USPAT; US-PGPUB	2003/05/30 09:02
-	7	mems and sacrificial and (cavity or void)	DERWENT	2003/04/29 12:54
-	33	mems and sacrificial	DERWENT	2003/04/30 12:00
-	2	mems and sacrificial	JPO	2003/04/29 12:59
-	4	mems and (void or cavity)	JPO	2003/04/29 12:59
-	109	(mems and (void or cavity or recess) and (substrate or silicon)).clm.	USPAT; US-PGPUB	2003/04/29 14:25
-	22	sacrificial and (wafer near3 bond$3)	DERWENT	2003/04/30 12:10
-	1	release and silicon and dioxide and (wafer near3 bond$3)	DERWENT	2003/04/30 12:08
-	4	(release or sacrificial or void or cavity) and silicon and dioxide and (substrate near3 bond$3)	DERWENT	2003/04/30 12:09
-	708	sacrificial and (wafer near3 bond$3)	USPAT; US-PGPUB	2003/04/30 12:11
-	366	sacrificial and (wafer near3 bond$3) and (silicon adj dioxide) and (releas$3 or etch$3)	USPAT; US-PGPUB	2003/05/30 10:12
-	5	(sacrificial and (wafer near3 bond$3) and (silicon adj dioxide) and (releas$3 or etch$3)).clm.	USPAT; US-PGPUB	2003/04/30 12:14
-	195	(sacrificial and (wafer near3 bond$3) and mems)	USPAT; US-PGPUB	2003/04/30 12:15
-	3	(("6417743") or ("6463339") or ("6348788")).PN.	USPAT; US-PGPUB	2003/05/01 09:52
-	1	("6159385").PN.	USPAT; US-PGPUB	2003/05/01 10:00
-	1	("6417743").PN.	USPAT; US-PGPUB	2003/05/01 10:00
-	12	((216/2).CCLS.) and (void or release or cavity) and MEM	USPAT; US-PGPUB	2003/05/01 10:02
-	79	((216/2).CCLS.) and (void or release or cavity) and (MEM or "MEM's")	USPAT; US-PGPUB	2003/05/01 10:03
-	240	((216/2).CCLS.) and (void or release or cavity or well) and silicon adj dioxide	USPAT; US-PGPUB	2003/05/27 13:40
-	215	((216/2).CCLS.) and (micromechanical or MEMS or micro-electromechanical or microelectromechanical)	USPAT; US-PGPUB	2003/05/27 14:03
-	1009	(micromechanical or MEMS or micro-electromechanical or microelectromechanical or micro-mechanical).ti.	USPAT; US-PGPUB	2003/05/30 10:03
-	1039	(micromechanical or MEMS or micro-electromechanical or microelectromechanical micro-electro-mechanical or micro-mechanical).ti.	USPAT; US-PGPUB	2003/05/27 14:07
-	874	(micromechanical or MEMS or micro-electromechanical or microelectromechanical micro-electro-mechanical or micro-mechanical).ti. and (cavity or void or recess or well)	USPAT; US-PGPUB	2003/05/30 10:07
-	49	(mems and (cavity or void or recess)).ab.	USPAT; US-PGPUB	2003/05/30 09:03
-	195	(microstructures or MEMS).ti. and (void or cavity or recess)	USPAT; US-PGPUB	2003/05/30 09:48
-	9	("5198390" | "5314572" | "5364497" | "5543013" | "5637539" | "5747353" | "5824177" | "5879963" | "6020215").PN.	USPAT	2003/05/30 09:41
-	325	wafer same etch$3 same silicon same (oxide or dioxide) same cavity	USPAT; US-PGPUB	2003/05/30 09:52

-	59	method same suspended same structure? same silicon	USPAT; US-PGPUB	2003/05/30 09:54
-	1269	(micromechanical or MEMS or microstructure? or micro-electromechanical or microelectromechanical or micro-mechanical).ti.	USPAT; US-PGPUB	2003/05/30 10:04
-	89	(micromechanical or MEMS or microstructure? or micro-electromechanical or microelectromechanical or micro-mechanical).ti.	JPO	2003/05/30 10:04
-	149	(micromechanical or MEMS or micro-electromechanical or microelectromechanical micro-electro-mechanical or micro-mechanical or microstructures or microstructure or suspended).ti. and (cavity or void or recess or well) and MEMS and wafer and silicon	USPAT; US-PGPUB	2003/05/30 10:09
-	701	(wafer same (silicon adj $2oxide) same etch$3) and (micromechanical or mems or microstructure? or micro-mechanical)	USPAT; US-PGPUB	2003/05/30 10:37
-	4	("5578976" | "5585311" | "5646432" | "5658698").PN.	USPAT	2003/05/30 10:34
-	82	(sealed adj cavity) same (wafer or substrate) same ($2oxide or dielectric or insulat$3)	USPAT; US-PGPUB	2003/06/02 17:09
-	235	(sealed adj cavity) and suspended and (structure or mechanical or etch$3)	USPAT; US-PGPUB	2003/06/02 16:08
-	1	"6465355"	DERWENT	2003/06/02 16:02
-	1	2003-310327.NRAN.	DERWENT	2003/06/02 16:02
-	2637	cavity and suspended and (structure or mechanical or micromachin$3) and etch$3	USPAT; US-PGPUB	2003/06/02 16:24
-	62	(cavity and micromachin$3).ab. and etch$3	USPAT; US-PGPUB	2003/06/02 16:23
-	3	(void and micromachin$3).ab. and etch$3	USPAT; US-PGPUB	2003/06/02 16:23
-	365	void and micromachin$3 and etch$3	USPAT; US-PGPUB	2003/06/02 16:42
-	54	(cavity and suspended and (structure or mechanical or micromachin$3)).ab.	USPAT; US-PGPUB	2003/06/02 16:25
-	5	svoronos.in.	USPAT; US-PGPUB	2003/06/02 16:43
-	213	(harris adj richard).in.	USPAT; US-PGPUB	2003/06/02 16:47
-	35	(kretschmann).in.	USPAT; US-PGPUB	2003/06/02 16:47
-	4163	MEMS and (remov$3 or etch$3)	USPAT; US-PGPUB	2003/06/02 17:00
-	111	(mems and (void or cavity) and (substrate or silicon)).clm.	USPAT; US-PGPUB	2003/06/02 17:00
-	393	(438/48).CCLS.	USPAT; US-PGPUB	2003/06/02 17:45
-	79	((438/48).CCLS.) and (cavity or void or recess)	USPAT; US-PGPUB	2003/06/02 17:14
-	302	(438/52).CCLS.	USPAT; US-PGPUB	2003/06/02 18:03
-	186	(438/51).CCLS.	USPAT; US-PGPUB	2003/06/02 18:13
-	154	((438/51).CCLS.) not ((438/52).CCLS.)	USPAT; US-PGPUB	2003/06/02 18:04
-	152	(438/456).CCLS.	USPAT; US-PGPUB	2003/06/02 18:14
-	591	(438/455).CCLS.	USPAT; US-PGPUB	2003/06/02 18:15
-	548	((438/455).CCLS.) not ((438/456).CCLS.)	USPAT; US-PGPUB	2003/06/02 18:16